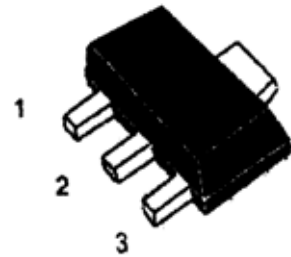

2SD1664

NPN EPITAXIAL SILICON TRANSISTOR

ABSOLUTE MAXIMUM RATINGS(Ta=25)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	40	V
Collector-Emitter Voltage	V _{CEO}	32	V
Emitter -Base Voltage	V _{EBO}	5	V
Collector Current	I _c	1	A(DC)
		2	A(Pulse))
Collector power Dissipation	P _c	0.5	W
		2	W
Junction Temperature	T _J	150	
Storage Temperature	T _{STG}	-55 ~150	

SOT-89



1,Base 2,Collector 3, Emitter

ELECTRCAL CHARACTERISTICS(Ta=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c = 50 μ A,I _E = 0	40			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _c = 1mA,	32			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 50 μ A	5			V
Collector-Cutoff Current	I _{CB0}	V _{CB} = 20V,I _E =0			0.5	μ A
Emitter-Cutoff Current	I _{EBO}	V _{EB} = 4V,I _c =0			0.5	μ A
*DC Current Gain	H _{fe}	V _{CE} = 3V,I _c = 100mA	82		390	
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c = 500mA,I _B = 50mA		0.15	0.4	V
Current Gain-Bandwidth Product	f _T	V _{CE} = 5V,I _E = 50mA		150		MHZ
Output Capacitance	C _{OB}	V _{CB} = 10V,I _E =0,f=1MHZ		15		pF

H_{FE} CLASSIFICATION

Classification	P	Q	R
H _{FE}	82-180	120-270	180-390